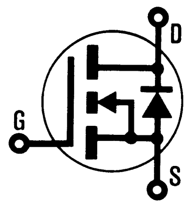
INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS IRFZ20 IRFZ22

N-Channel 50 Volt Power MOSFETs



50 Volt, 0.1 Ohm HEXFET TO-220AB Plastic Package

The HEXFET technology has expanded its product base to serve the low voltage, very low $R_{DS(on)}$ MOSFET transistor requirements. International Rectifier's highly efficient geometry and unique processing of the HEXFET have been combined to create the lowest on resistance per device performance. In addition to this feature all HEXFETs have documented reliability and parts per million quality!

The HEXFET transistors also offer all of the well established advantages of MOSFETs such as voltage control, freedom from second breakdown, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, high energy pulse circuits, and in systems that are operated from low voltage batteries, such as automotive, portable equipment, etc.

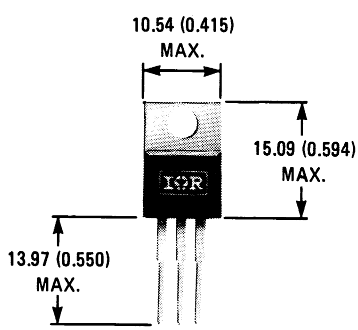
Features:

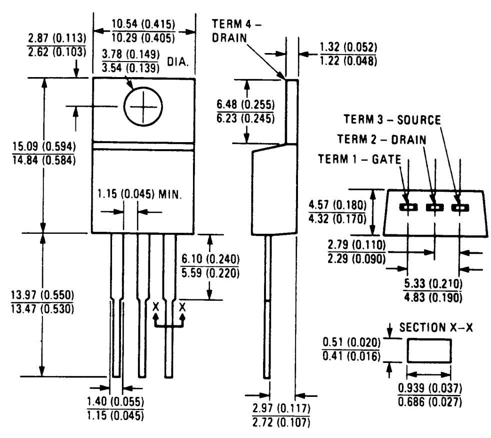
- Extremely Low $R_{DS(on)}$
- Compact Plastic Package
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability
- Parts Per Million Quality

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFZ20	50V	0.10Ω	15A
IRFZ22	50V	0.12Ω	14A

CASE STYLE AND DIMENSIONS



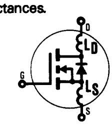


Case Style TO-220AB
Dimensions in Millimeters and (Inches)

Absolute Maximum Ratings

Parameter		IRFZ20	IRFZ22	Units
V_{DS}	Drain - Source Voltage ①	50	50	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 KΩ) ①	50	50	V
I_D @ T_C = 25°C	Continuous Drain Current	15	14	A
I_D @ T_C = 100°C	Continuous Drain Current	10	9.0	A
I_{DM}	Pulsed Drain Current ③	60	56	A
V_{GS}	Gate - Source Voltage	±20		V
P_D @ T_C = 25°C	Max. Power Dissipation	40 (See Fig. 14)		W
	Linear Derating Factor	0.32 (See Fig. 14)		W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH 60	56	A
T_J T_{stg}	Operating Junction and Storage Temperature Range	−55 to 150		°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)		°C

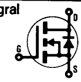
Electrical Characteristics @ T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRFZ20	50	—	—	V	V_{GS} = 0V
		IRFZ22	50	—	—	V	I_D = 250 μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250 μA
I_{GSS}	Gate-Source Leakage Forward	ALL	—	—	500	nA	V_{GS} = 20V
I_{GSS}	Gate-Source Leakage Reverse	ALL	—	—	−500	nA	V_{GS} = −20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	—	—	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			—	—	1000	μA	V_{DS} = Max. Rating × 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFZ20	15	—	—	A	V_{DS} > $I_{D(on)}$ × $R_{DS(on)max.}$, V_{GS} = 10V
		IRFZ22	14	—	—	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFZ20	—	0.080	0.100	Ω	V_{GS} = 10V, I_D = 9.0A
		IRFZ22	—	0.110	0.120	Ω	
g_{fs}	Forward Transconductance ②	ALL	5.0	6.0	—	S (℧)	V_{DS} > $I_{D(on)}$ × $R_{DS(on)}$ max., I_D = 9.0A
C_{iss}	Input Capacitance	ALL	—	560	850	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	—	250	350	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	—	60	100	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	—	15	30	ns	V_{DD} ≅ 25V, I_D = 9.0A, Z_o = 50Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	—	45	90	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	—	20	40	ns	
t_f	Fall Time	ALL	—	15	30	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	—	12	17	nC	V_{GS} = 10V, I_D = 20A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	—	9.0	—	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	—	3.0	—	nC	
L_D	Internal Drain Inductance	ALL	—	3.5	—	nH	Measured from the contact screw on tab to center of die. — Modified MOSFET symbol showing the internal device inductances. 
			—	4.5	—	nH	Measured from the drain lead, 6mm (0.25 in.) from package to center of die.
L_S	Internal Source Inductance	ALL	—	7.5	—	nH	Measured from the source lead, 6mm (0.25 in.) from package to source bonding pad.

Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	—	—	3.12	K/W	
R_{thCS}	Case-to-Sink	ALL	—	1.0	—	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	—	—	80	K/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFZ20	—	—	15	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
		IRFZ22	—	—	14	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFZ20	—	—	60	A	
		IRFZ22	—	—	56	A	
V_{SD}	Diode Forward Voltage ②	IRFZ20	—	—	1.25	V	T_C = 25°C, I_S = 15A, V_{GS} = 0V
		IRFZ22	—	—	1.1	V	T_C = 25°C, I_S = 14A, V_{GS} = 0V
t_{rr}	Reverse Recovery Time	ALL	—	100	—	ns	T_J = 150°C, I_F = 15A, dI_F/dt = 100A/μs
Q_{RR}	Reverse Recovered Charge	ALL	—	0.4	—	μC	T_J = 150°C, I_F = 15A, dI_F/dt = 100A/μs
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

① T_J = 25°C to 150°C. ② Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

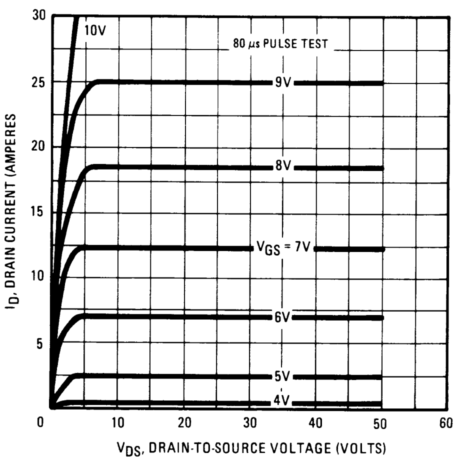


Fig. 1 — Typical Output Characteristics

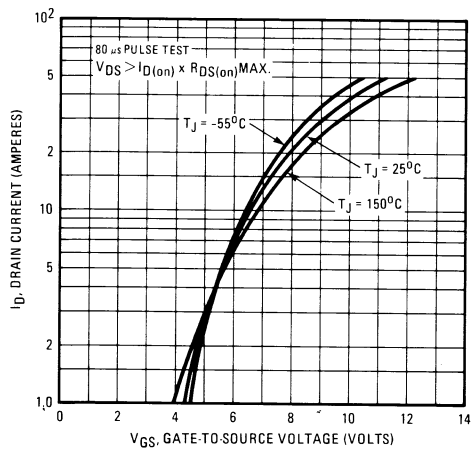


Fig. 2 — Typical Transfer Characteristics

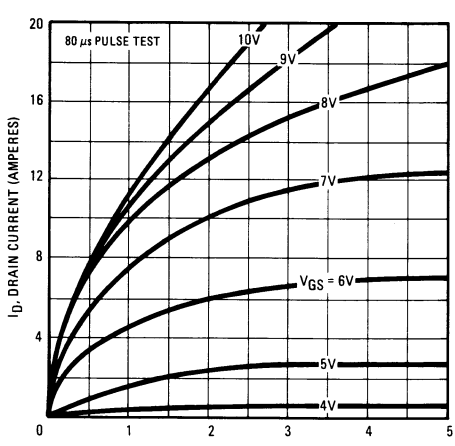


Fig. 3 — Typical Saturation Characteristics

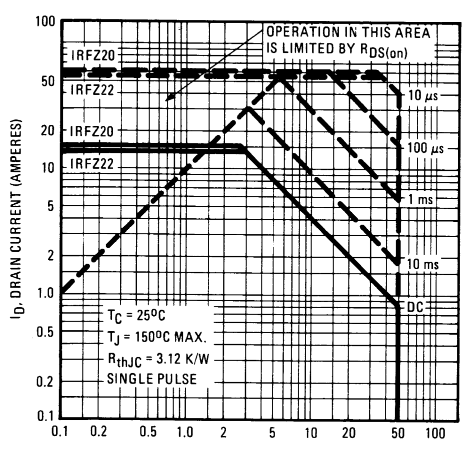


Fig. 4 — Maximum Safe Operating Area

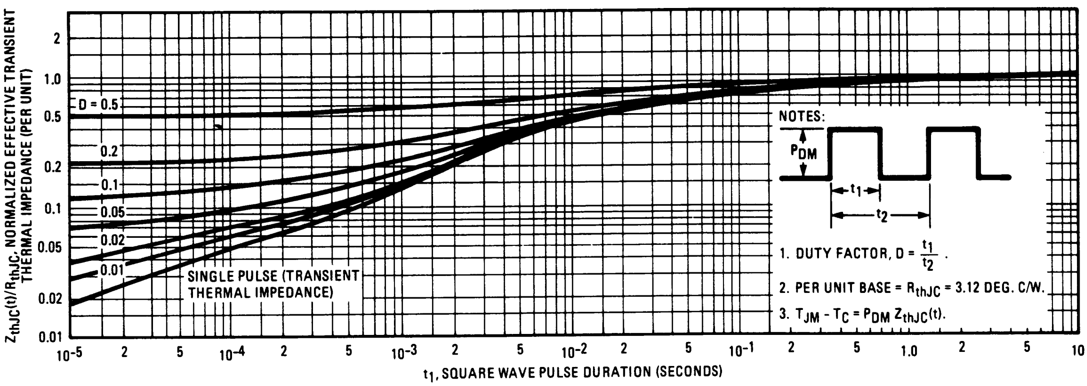


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

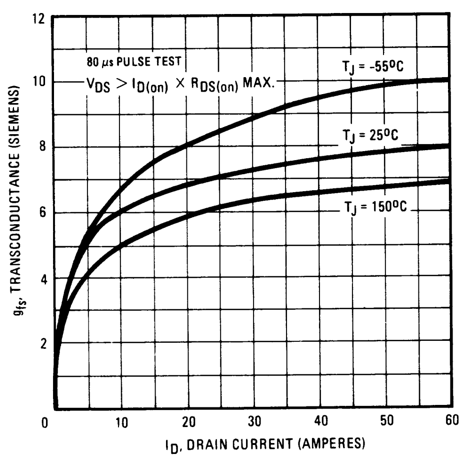


Fig. 6 — Typical Transconductance Vs. Drain Current

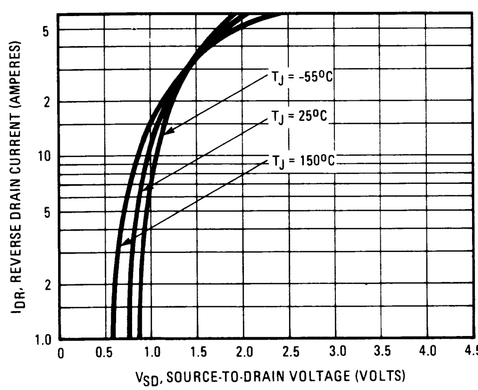


Fig. 7 — Typical Source-Drain Diode Forward Voltage

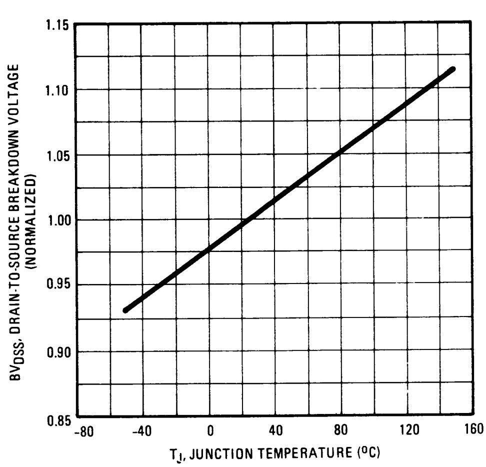


Fig. 8 — Breakdown Voltage Vs. Temperature

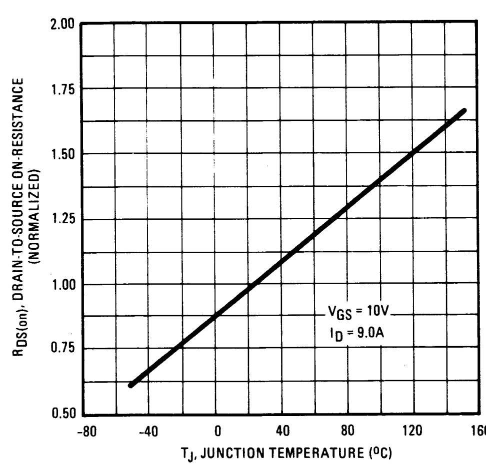


Fig. 9 — Normalized On-Resistance Vs. Temperature

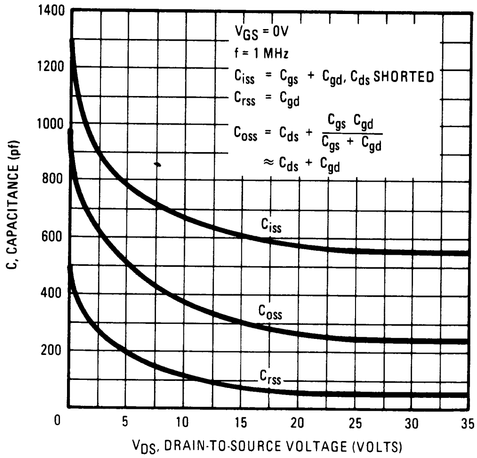


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

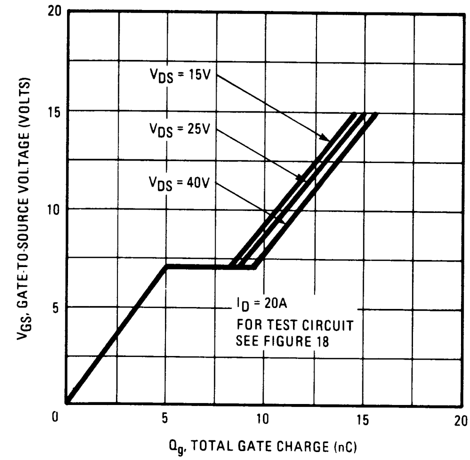


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

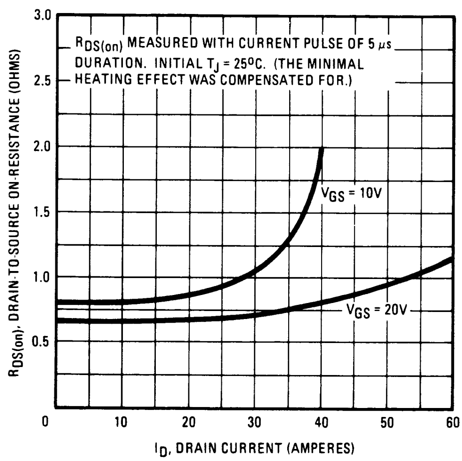


Fig. 12 — Typical On-Resistance Vs. Drain Current

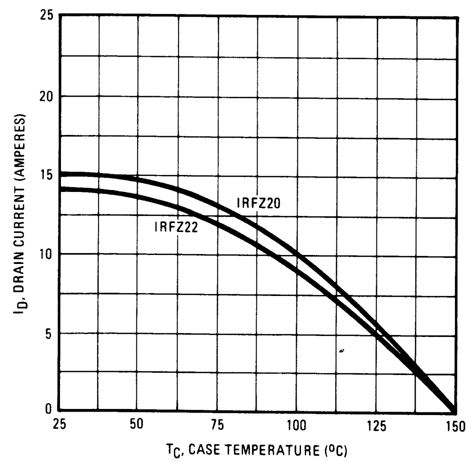


Fig. 13 — Maximum Drain Current Vs. Case Temperature

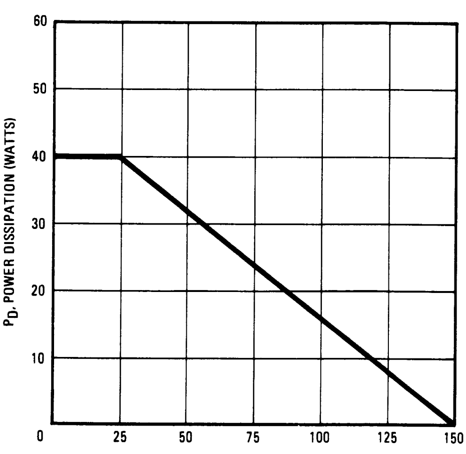


Fig. 14 — Power Vs. Temperature Derating Curve

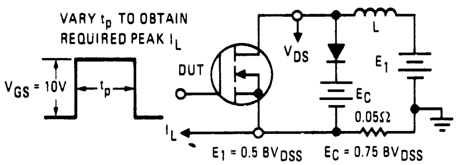


Fig. 15 – Clamped Inductive Test Circuit

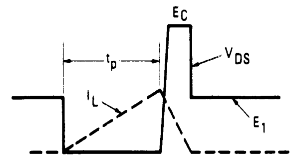


Fig. 16 – Clamped Inductive Waveforms

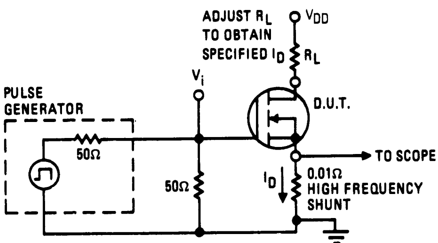


Fig. 17 – Switching Time Test Circuit

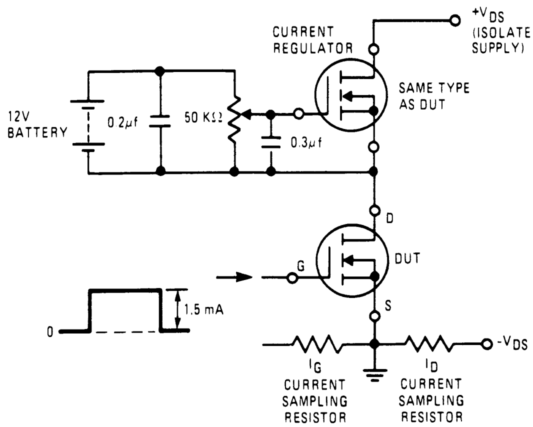


Fig. 18 – Gate Charge Test Circuit

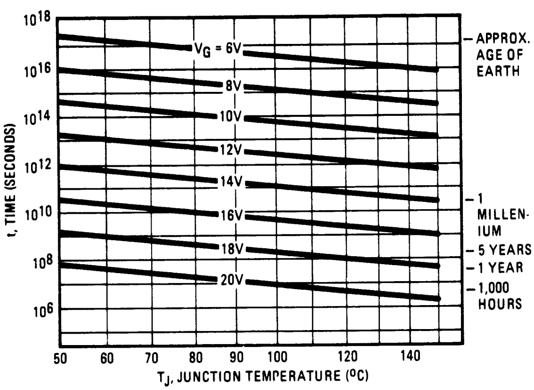


*Fig. 19 – Typical Time to Accumulated 1% Failure

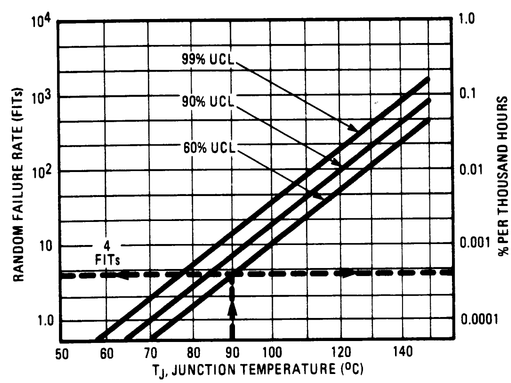


*Fig. 20 – Typical High Temperature Reverse Bias (HTRB) Failure Rate)

*The data shown is correct as of April 15, 1984. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.

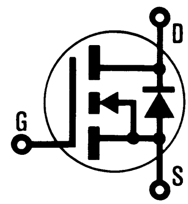
Data Sheet No. PD-9.414A

INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS

IRFZ30
IRFZ32

N-Channel 50 VOLT POWER MOSFETs



50 Volt, 0.05 Ohm HEXFET TO-220AB Plastic Package

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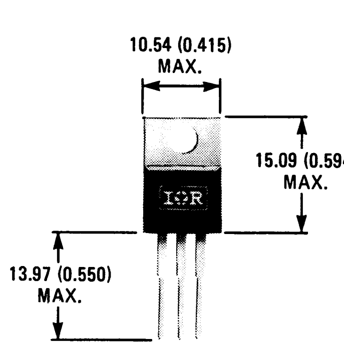
Features:

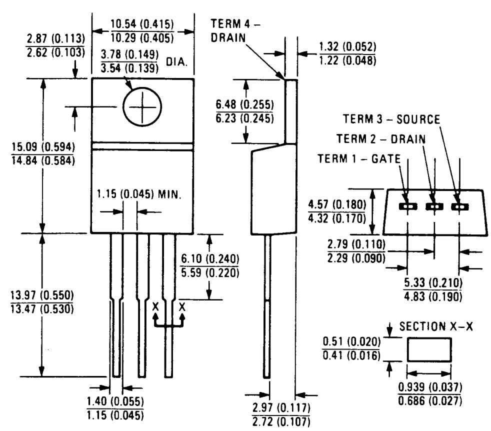
- Extremely Low $R_{DS(on)}$
- Compact Plastic Package
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability
- Parts Per Million Quality

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFZ30	50V	0.05Ω	30A
IRFZ32	50V	0.07Ω	25A

CASE STYLE AND DIMENSIONS





Case Style TO-220AB
Dimensions in Millimeters and (Inches)

IRFZ30, IRFZ32 Devices

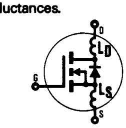
Absolute Maximum Ratings

Parameter		IRFZ30	IRFZ32	Units
V_{DS}	Drain - Source Voltage ①	50	50	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 KΩ) ①	50	50	V
I_D @ T_C = 25°C	Continuous Drain Current	30	25	A
I_D @ T_C = 100°C	Continuous Drain Current	19	16	A
I_{DM}	Pulsed Drain Current ③	80	60	A
V_{GS}	Gate - Source Voltage	±20		V
P_D @ T_C = 25°C	Max. Power Dissipation	75 (See Fig. 14)		W
	Linear Derating Factor	0.6 (See Fig. 14)		W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH 80	60	A
T_J T_{stg}	Operating Junction and Storage Temperature Range	−55 to 150		°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)		°C

Electrical Characteristics @ T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRFZ30	50	—	—	V	V_{GS} = 0V
		IRFZ32	50	—	—	V	I_D = 250 μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250 μA
I_{GSS}	Gate-Source Leakage Forward	ALL	—	—	500	nA	V_{GS} = 20V
I_{GSS}	Gate-Source Leakage Reverse	ALL	—	—	−500	nA	V_{GS} = −20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	—	—	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			—	—	1000	μA	V_{DS} = Max. Rating × 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFZ30	30	—	—	A	V_{DS} > $I_{D(on)}$ × $R_{DS(on)max.}$, V_{GS} = 10V
		IRFZ32	25	—	—	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFZ30	—	0.045	0.050	Ω	V_{GS} = 10V, I_D = 16A
		IRFZ32	—	0.065	0.070	Ω	
g_{fs}	Forward Transconductance ②	ALL	9.0	12	—	S(℧)	V_{DS} > $I_{D(on)}$ × $R_{DS(on)}$ max., I_D = 16A
C_{iss}	Input Capacitance	ALL	—	1250	1600	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz
C_{oss}	Output Capacitance	ALL	—	550	800	pF	See Fig. 10
C_{rss}	Reverse Transfer Capacitance	ALL	—	130	200	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	—	12	25	ns	V_{DD} ≅ 25V, I_D = 16A, Z_o = 50Ω
t_r	Rise Time	ALL	—	16	35	ns	See Fig. 17
$t_{d(off)}$	Turn-Off Delay Time	ALL	—	23	45	ns	(MOSFET switching times are essentially independent of operating temperature.)
t_f	Fall Time	ALL	—	16	35	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	—	26	30	nC	V_{GS} = 10V, I_D = 38A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	—	14	—	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	—	12	—	nC	
L_D	Internal Drain Inductance	ALL	—	3.5	—	nH	Measured from the contact screw on tab to center of die.
			—	4.5	—	nH	Measured from the drain lead, 6mm (0.25 in.) from package to center of die.
L_S	Internal Source Inductance	ALL	—	7.5	—	nH	Measured from the source lead, 6mm (0.25 in.) from package to source bonding pad.

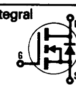
Modified MOSFET symbol showing the internal device inductances.



Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	—	—	1.67	K/W	
R_{thCS}	Case-to-Sink	ALL	—	1.0	—	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	—	—	80	K/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFZ30	—	—	30	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
		IRFZ32	—	—	25	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFZ30	—	—	80	A	
		IRFZ32	—	—	60	A	
V_{SD}	Diode Forward Voltage ②	IRFZ30	—	—	1.6	V	T_C = 25°C, I_S = 30A, V_{GS} = 0V
		IRFZ32	—	—	1.5	V	T_C = 25°C, I_S = 25A, V_{GS} = 0V
t_{rr}	Reverse Recovery Time	ALL	—	160	—	ns	T_J = 150°C, I_F = 30A, dI_F/dt = 100A/μs
Q_{RR}	Reverse Recovered Charge	ALL	—	1.5	—	μC	T_J = 150°C, I_F = 30A, dI_F/dt = 100A/μs
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L_S + L_D.				

① T_J = 25°C to 150°C. ② Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

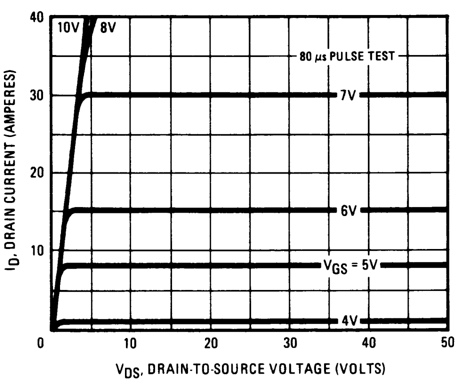


Fig. 1 — Typical Output Characteristics

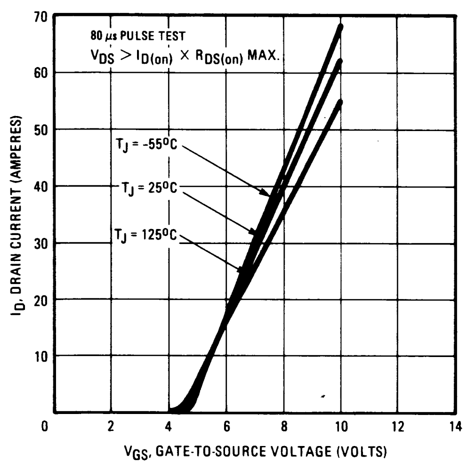


Fig. 2 — Typical Transfer Characteristics

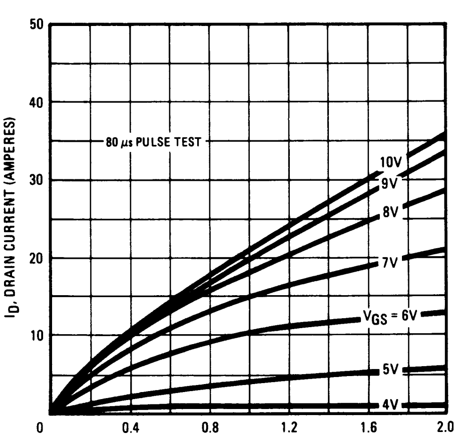


Fig. 3 — Typical Saturation Characteristics

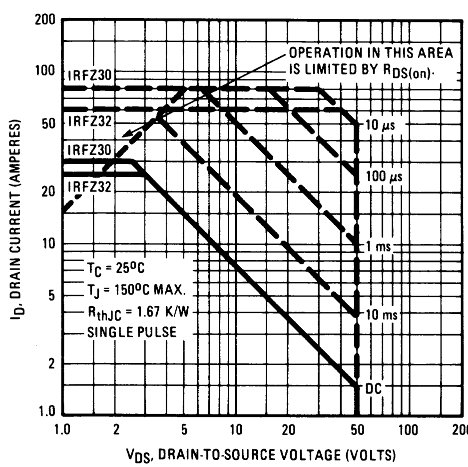


Fig. 4 — Maximum Safe Operating Area

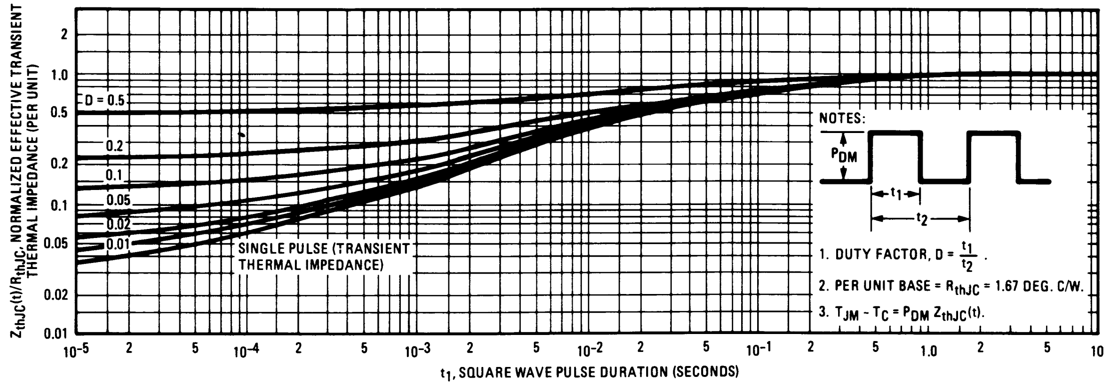


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

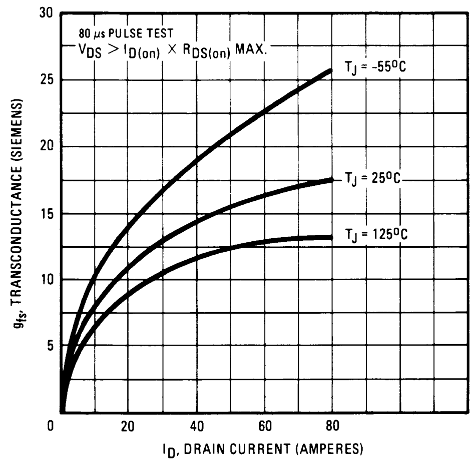


Fig. 6 Typical Transconductance Vs. Drain Current

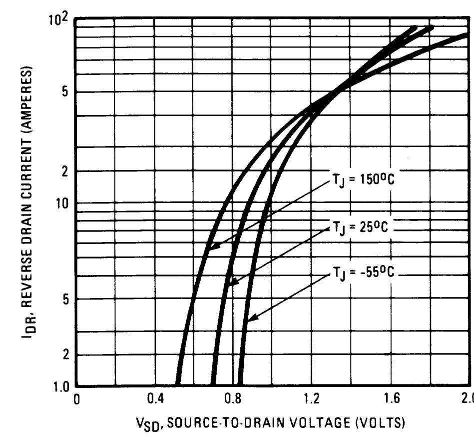


Fig. 7 — Typical Source-Drain Diode Forward Voltage

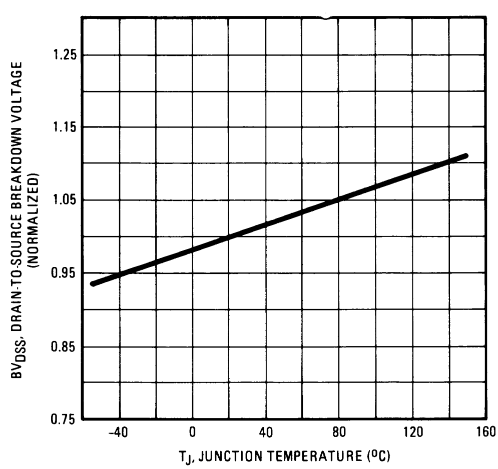


Fig. 8 — Breakdown Voltage Vs. Temperature

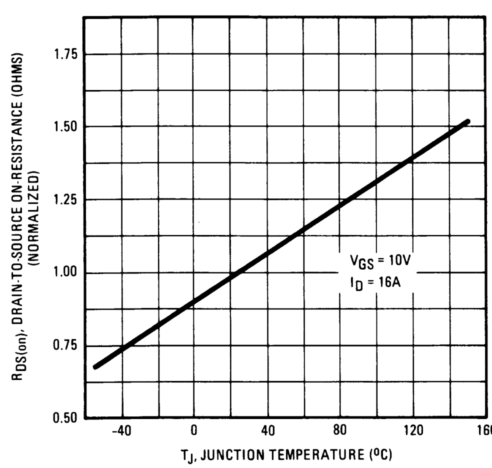


Fig. 9 — Normalized On-Resistance Vs. Temperature

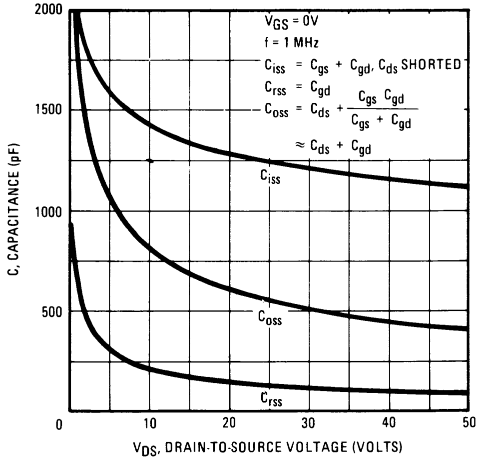


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

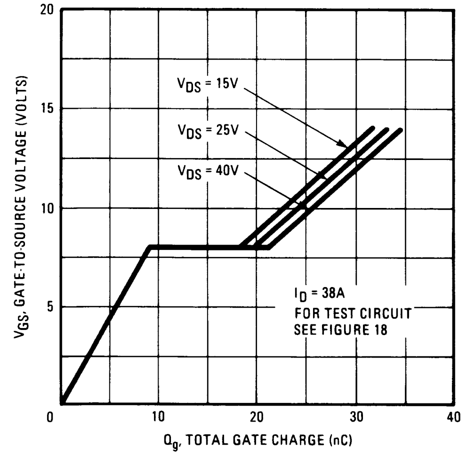


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

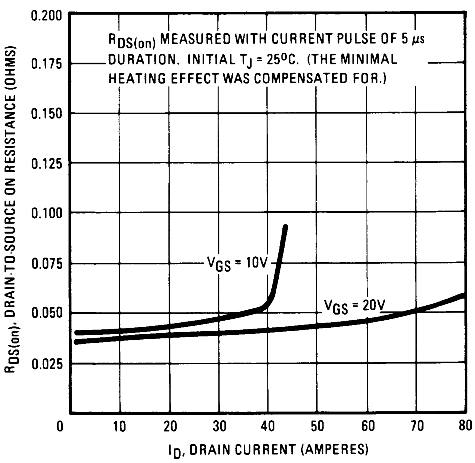


Fig. 12 — Typical On-Resistance Vs. Drain Current

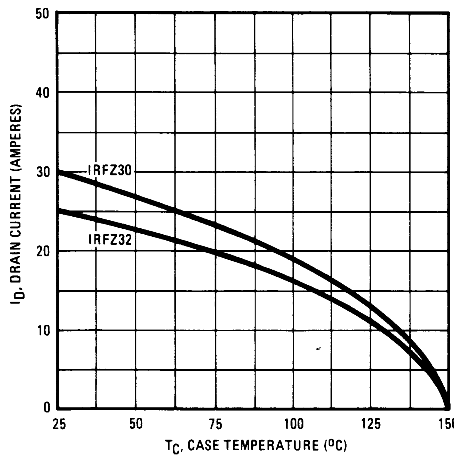


Fig. 13 — Maximum Drain Current Vs. Case Temperature

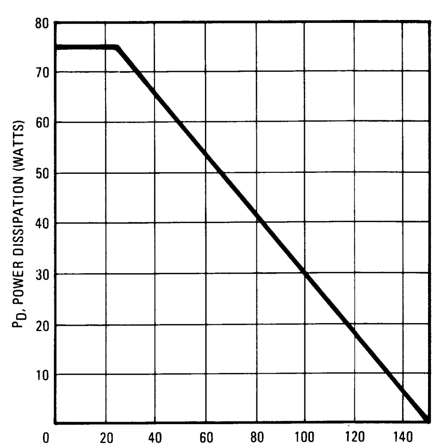


Fig. 14 — Power Vs. Temperature Derating Curve

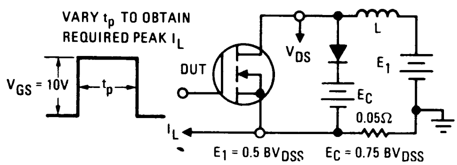


Fig. 15 — Clamped Inductive Test Circuit

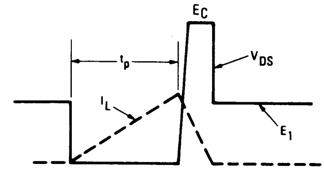


Fig. 16 — Clamped Inductive Waveforms

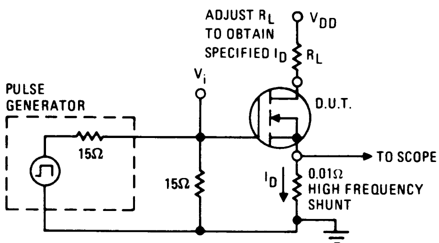


Fig. 17 — Switching Time Test Circuit

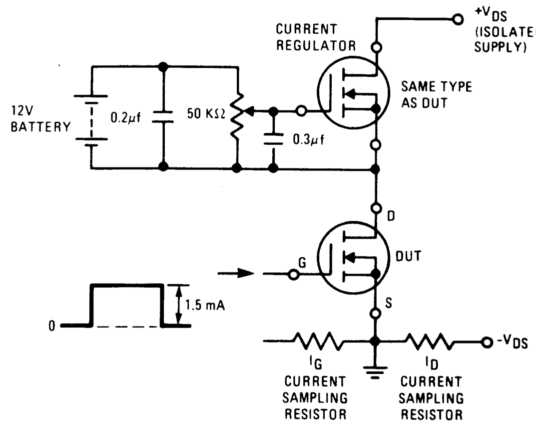


Fig. 18 — Gate Charge Test Circuit

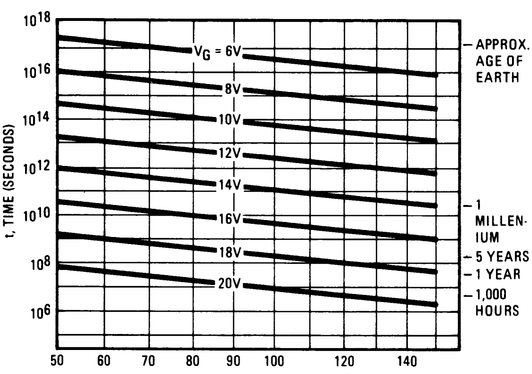


***Fig. 19 — Typical Time to Accumulated 1% Failure**

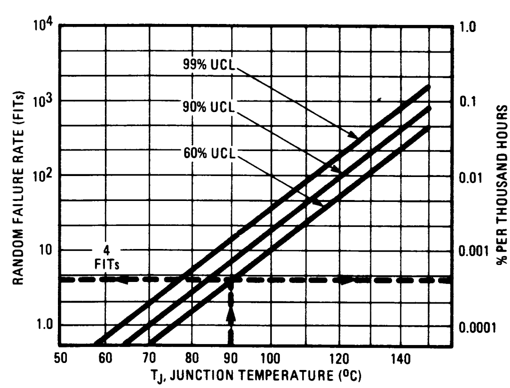


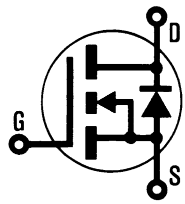
***Fig. 20 — Typical High Temperature Reverse Bias (HTRB) Failure Rate**

*The data shown is correct as of April 15, 1984. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.

INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS IRFZ40 IRFZ42

N-Channel 50 VOLT POWER MOSFETs



50 Volt, 0.028 Ohm HEXFET TO-220AB Plastic Package

The HEXFET technology has expanded its product base to serve the low voltage, very low $R_{DS(on)}$ MOSFET transistor requirements. International Rectifier's highly efficient geometry and unique processing of the HEXFET have been combined to create the lowest on resistance per device performance. In addition to this feature all HEXFETs have documented reliability and parts per million quality!

The HEXFET transistors also offer all of the well established advantages of MOSFETs such as voltage control, freedom from second breakdown, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, high energy pulse circuits, and in systems that are operated from low voltage batteries, such as automotive, portable equipment, etc.

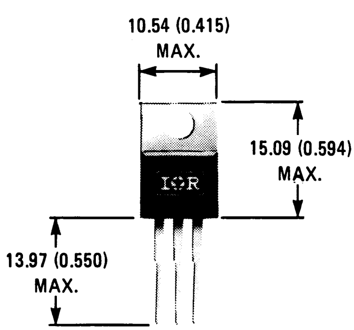
Features:

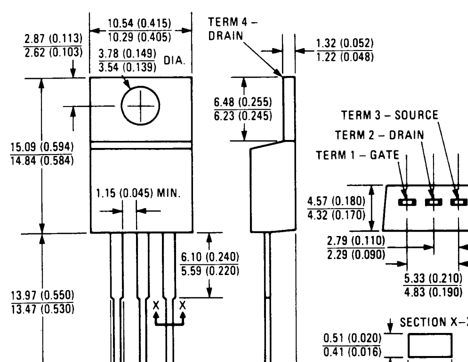
- Extremely Low $R_{DS(on)}$
- Compact Plastic Package
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability
- Parts Per Million Quality

Product Summary

PART NUMBER	V_{DS}	$R_{DS(ON)}$	I_D
IRFZ40	50V	0.028Ω	51A
IRFZ42	50V	0.035Ω	46A

CASE STYLE AND DIMENSIONS





Case Style TO-220AB
Dimensions in Millimeters and (Inches)

IRFZ40, IRFZ42 Devices

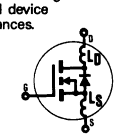
Absolute Maximum Ratings

Parameter		IRFZ40	IRFZ42	Units
V_{DS}	Drain - Source Voltage ①	50	50	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 KΩ) ①	50	50	V
I_D @ T_C = 25°C	Continuous Drain Current	51	46	A
I_D @ T_C = 100°C	Continuous Drain Current	32	29	A
I_{DM}	Pulsed Drain Current ③	160	145	A
V_{GS}	Gate - Source Voltage	±20		V
P_D @ T_C = 25°C	Max. Power Dissipation	125 (See Fig. 14)		W
	Linear Derating Factor	1.0 (See Fig. 14)		W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH 160	145	A
T_J T_{stg}	Operating Junction and Storage Temperature Range	−55 to 150		°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)		°C

Electrical Characteristics @ T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRFZ40	50	–	–	V	V_{GS} = 0V
		IRFZ42	50	–	–	V	I_D = 250 μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	–	4.0	V	V_{DS} = V_{GS}, I_D = 250 μA
I_{GSS}	Gate-Source Leakage Forward	ALL	–	–	500	nA	V_{GS} = 20V
I_{GSS}	Gate-Source Leakage Reverse	ALL	–	–	−500	nA	V_{GS} = −20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	–	–	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			–	–	1000	μA	V_{DS} = Max. Rating × 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFZ40	51	–	–	A	V_{DS} > $I_{D(on)}$ × $R_{DS(on)max.}$, V_{GS} = 10V
		IRFZ42	45	–	–	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFZ40	–	0.024	0.028	Ω	V_{GS} = 10V, I_D = 29A
		IRFZ42	–	0.030	0.035	Ω	
g_{fs}	Forward Transconductance ②	ALL	17	22	–	S(Ω)	V_{DS} > $I_{D(on)}$ × $R_{DS(on)}$ max., I_D = 29A
C_{iss}	Input Capacitance	ALL	–	2350	3000	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz
C_{oss}	Output Capacitance	ALL	–	920	1200	pF	See Fig. 10
C_{rss}	Reverse Transfer Capacitance	ALL	–	250	400	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	–	18	25	ns	V_{DD} ≅ 25V, I_D = 29A, Z_o = 4.7Ω
t_r	Rise Time	ALL	–	25	60	ns	See Fig. 17
$t_{d(off)}$	Turn-Off Delay Time	ALL	–	35	70	ns	(MOSFET switching times are essentially independent of operating temperature.)
t_f	Fall Time	ALL	–	12	25	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	–	40	60	nC	V_{GS} = 10V, I_D = 64A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	–	22	–	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	–	18	–	nC	
L_D	Internal Drain Inductance	ALL	–	3.5	–	nH	Measured from the contact screw on tab to center of die.
			–	4.5	–	nH	Measured from the drain lead, 6mm (0.25 in.) from package to center of die.
L_S	Internal Source Inductance	ALL	–	7.5	–	nH	Measured from the source lead, 6mm (0.25 in.) from package to source bonding pad.

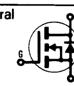
Modified MOSFET symbol showing the internal device inductances.



Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	–	–	1.0	K/W	
R_{thCS}	Case-to-Sink	ALL	–	1.0	–	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	–	–	80	K/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFZ40	—	—	51	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
		IRFZ42	—	—	46	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFZ40	—	—	160	A	
		IRFZ42	—	—	145	A	
V_{SD}	Diode Forward Voltage ②	IRFZ40	—	—	2.5	V	T_C = 25°C, I_S = 51A, V_{GS} = 0V
		IRFZ42	—	—	2.2	V	T_C = 25°C, I_S = 46A, V_{GS} = 0V
t_{rr}	Reverse Recovery Time	ALL	—	350	—	ns	T_J = 150°C, I_F = 51A, dI_F/dt = 100A/μs
Q_{RR}	Reverse Recovered Charge	ALL	—	2.1	—	μC	T_J = 150°C, I_F = 51A, dI_F/dt = 100A/μs
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L_S + L_D.				

① T_J = 25°C to 150°C. ② Pulse Test: Pulse width ⩽ 300μs, Duty Cycle ⩽ 2%. ③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5). TO-220A

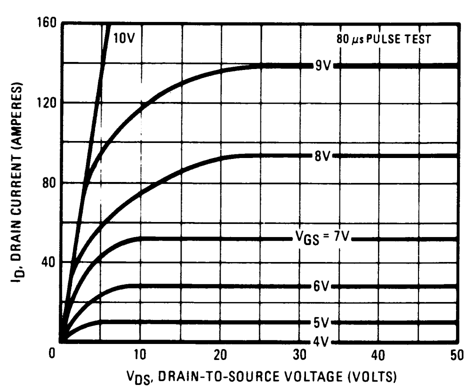


Fig. 1 — Typical Output Characteristics

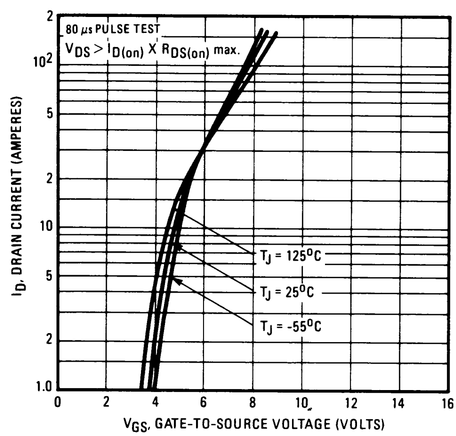


Fig. 2 — Typical Transfer Characteristics

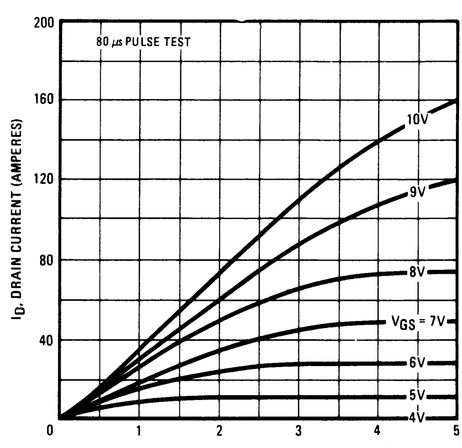


Fig. 3 — Typical Saturation Characteristics

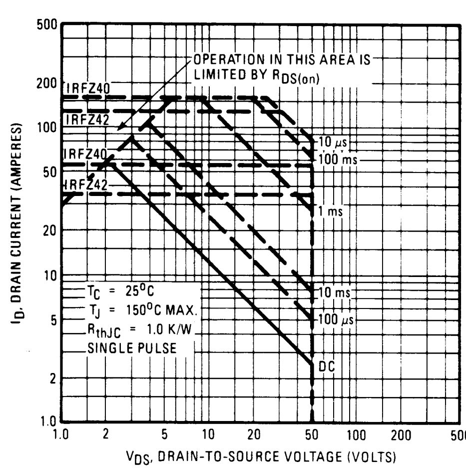


Fig. 4 — Maximum Safe Operating Area

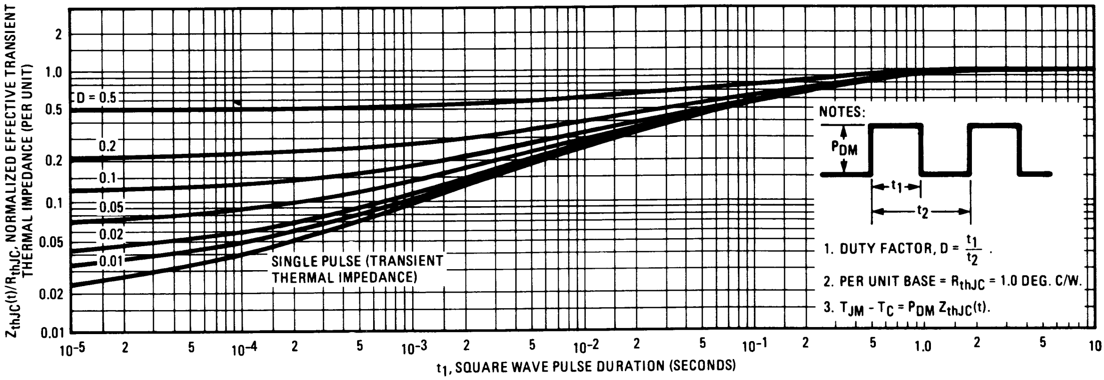


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-toCase Vs. Pulse Duration

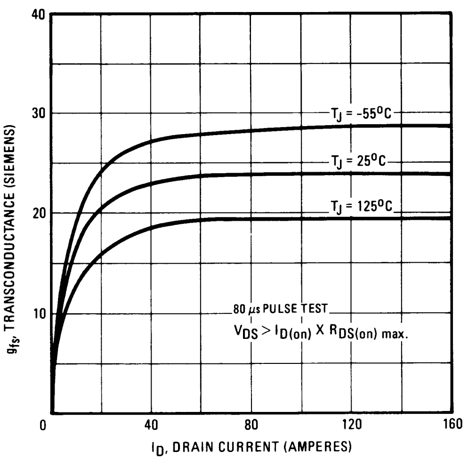


Fig. 6 — Typical Transconductance Vs. Drain Current

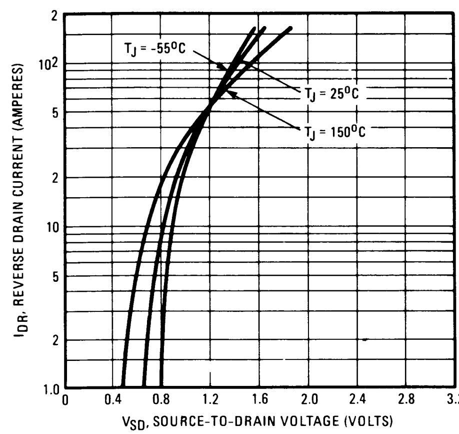


Fig. 7 — Typical Source-Drain Diode Forward Voltage

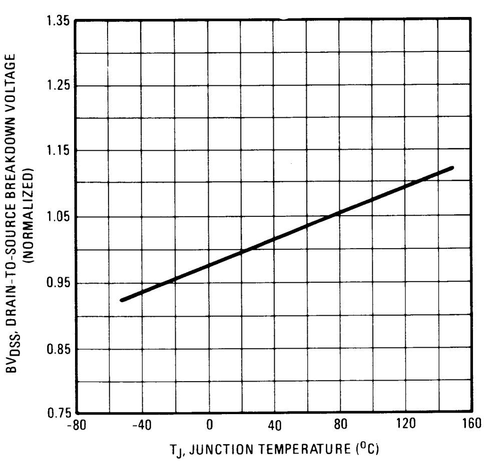


Fig. 8 — Breakdown Voltage Vs. Temperature

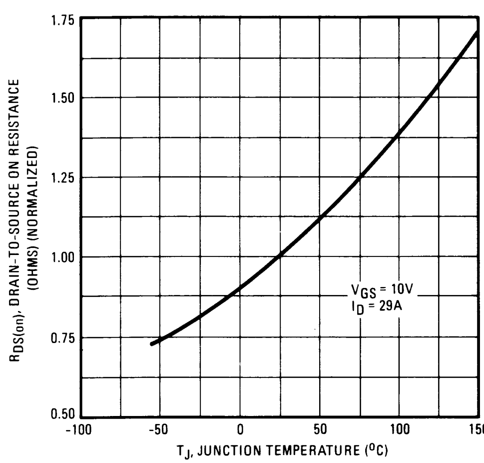


Fig. 9 — Normalized On-Resistance Vs. Temperature

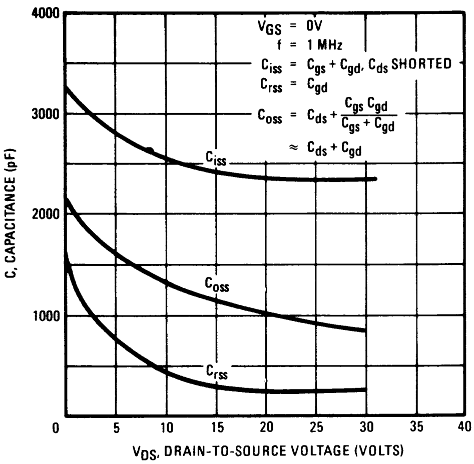


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

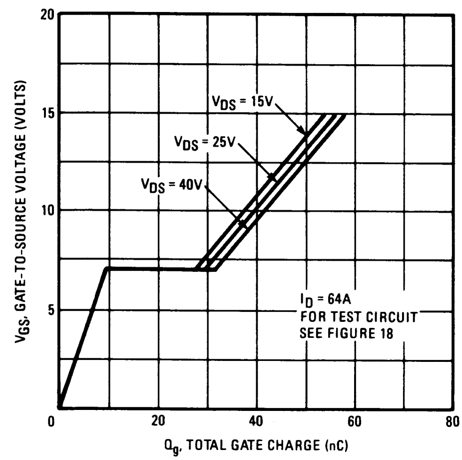


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

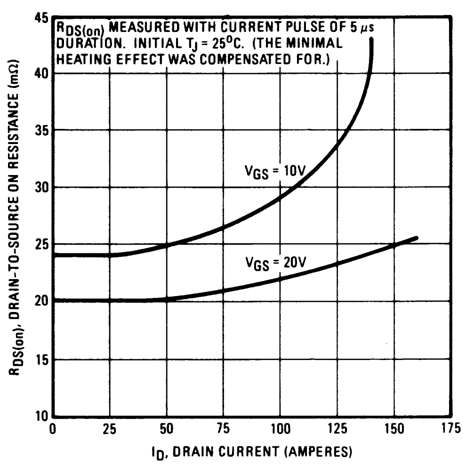


Fig. 12 — Typical On-Resistance Vs. Drain Current

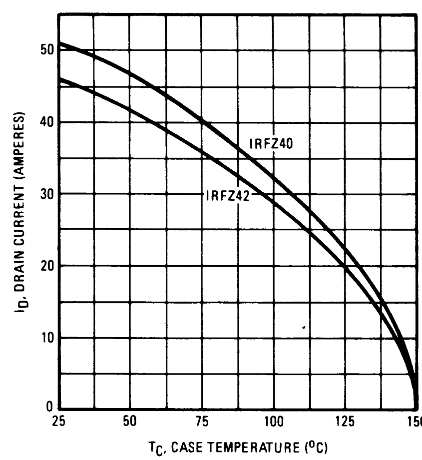


Fig. 13 — Maximum Drain Current Vs. Case Temperature

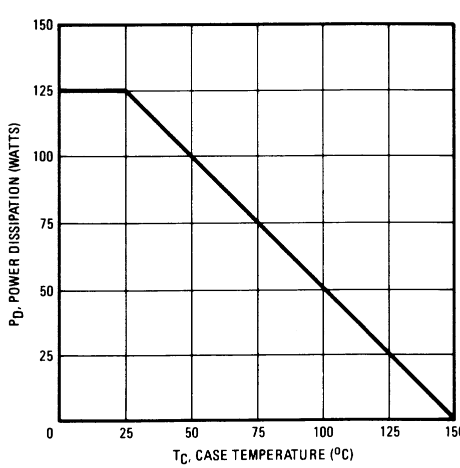


Fig. 14 — Power Vs. Temperature Derating Curve

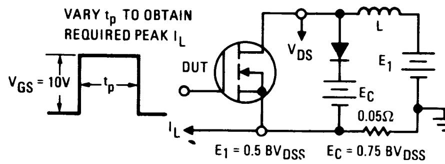


Fig. 15 — Clamped Inductive Test Circuit

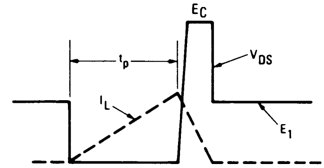


Fig. 16 — Clamped Inductive Waveforms

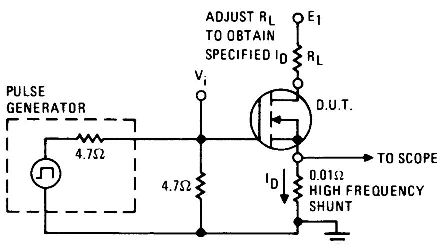


Fig. 17 — Switching Time Test Circuit

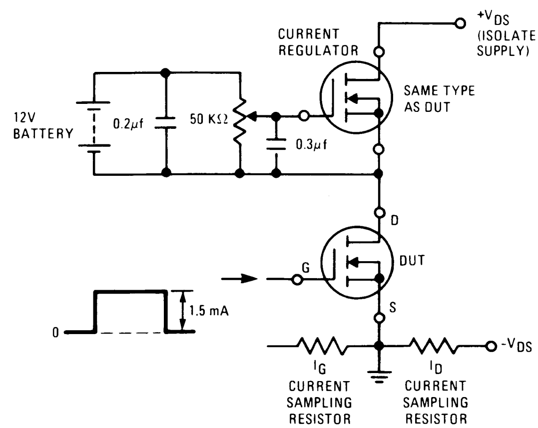


Fig. 18 — Gate Charge Test Circuit

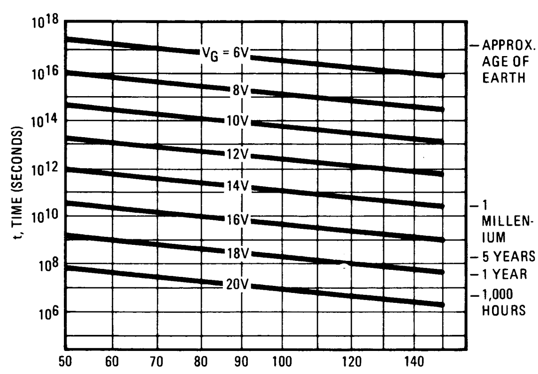


***Fig. 19 — Typical Time to Accumulated 1% Failure**

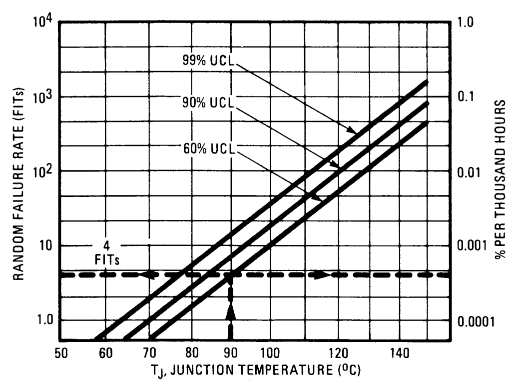


***Fig. 20 — Typical High Temperature Reverse Bias (HTRB) Failure Rate**

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